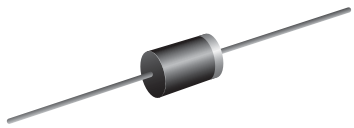
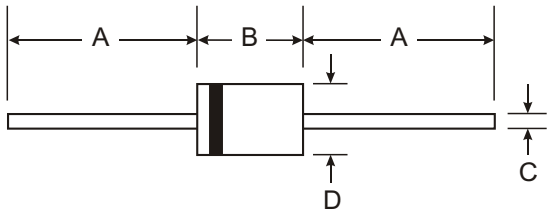
1N5823 - 1N5825

SCHOTTKY BARRIER RECTIFIER DIODE

VOLTAGE RANGE: 20 - 40V
CURRENT: 5.0 A





Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

DO-201AD		
Dim	**Min**	**Max**
A	25.40	—
B	8.50	9.53
C	0.96	1.06
D	4.80	5.21
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N5823	1N5824	1N5825	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified Output Current @T_L = 100°C (Note 1)	I_O	5.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150			A
Forward Voltage @I_F = 5.0A	V_{FM}	0.55			V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	0.5 50			mA
Typical Junction Capacitance (Note 2)	C_j	500			pF
Typical Thermal Resistance (Note 1)	$R_{\theta JA}$	10			°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150			°C

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

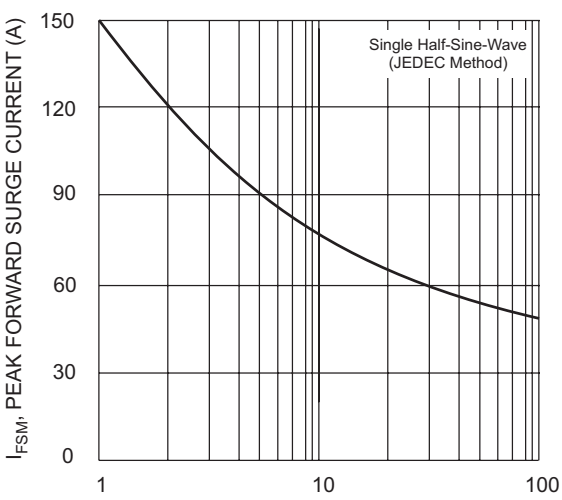


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

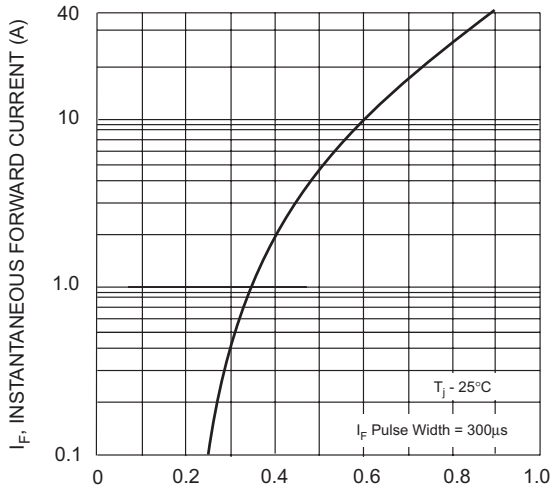


Fig. 2 Typical Forward Characteristics

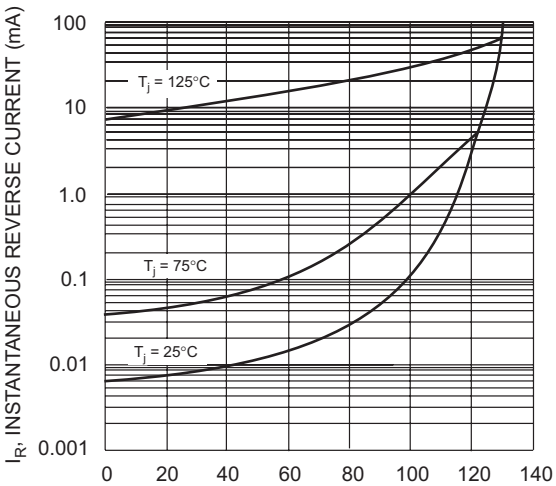


Fig. 5 Typical Reverse Characteristics

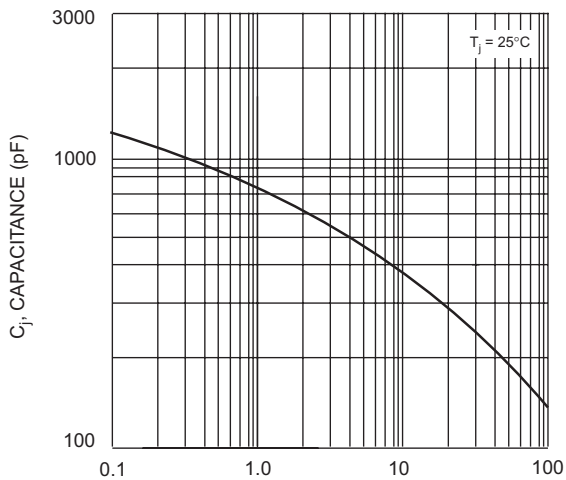


Fig. 4 Typical Junction Capacitance